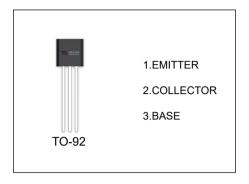


BC212 TRANSISTOR (PNP)

FEATURES

General Purpose Switching and Amplification.



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
BC212	TO-92	Bulk	1000pcs/Bag
BC212-TA	TO-92	Tape	2000pcs/Box

MAXIMUM RATINGS (T_a=25℃ unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	-60	V
V _{CEO}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-5	V
Ic	Collector Current -Continuous	-0.1	А
Pc	Collector Power Dissipation	0.35	W
R _{θ JA}	Thermal Resistance From Junction To Ambient	357	°C /W
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C



T_a =25 $^{\circ}$ C unless otherwise specified

Parameter	Symbol	Test conditions		Min	Тур	Max	Unit
Collector-base breakdown voltage	llector-base breakdown voltage V _{(BR)CBO} I _C = -0.01mA,I _E =0		-60			V	
ollector-emitter breakdown voltage V _{(BR)CEO} I _C =-2mA,I _B =0		-50			V		
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =-0.01mA,I _C =0		-5			V
Collector cut-off current	I _{CBO}	V _{CB} =-30V,I _E =0				-15	nA
Collector cut-off current	I _{CEO}	V _{CE} =-30V,I _B =0				-0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} =-4V,I _C =0				-15	nA
	h _{FE}	V _{CE} =-5V, I _C =-2mA	BC212	140		600	
DC current gain			BC212B	140		400	
			BC212C	350		600	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-100mA,I _B =-5mA				-0.6	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-100mA,I _B =-5mA				-1.2	V
Base-emitter voltage	V_{BE}	V_{CE} =-5V, I_{C} =-2mA				-0.72	V
Transition frequency	f _T	V _{CE} =-5V,I _C =-10mA,f=100MHz		200			MHz
Collector output capacitance	C _{ob}	V _{CB} =-10V,I _C =0, f=1MHz				6	pF